Medium Power Transistor (32V, 1A)

2SD1664 / 2SD1858

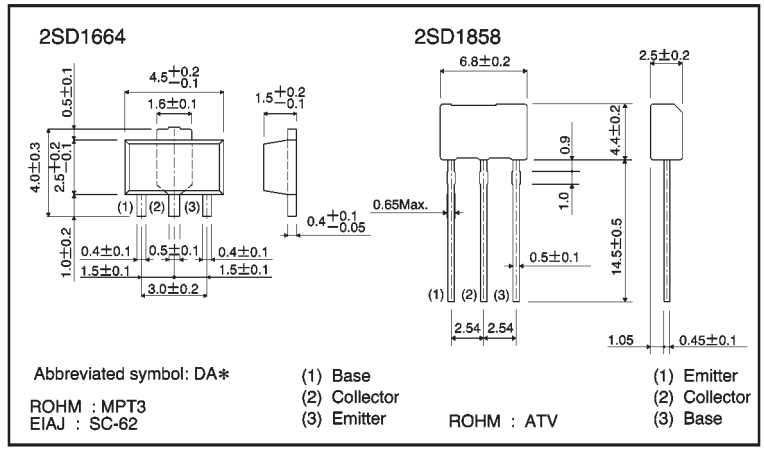
●Features

1) Low $V_{CE(sat)}$, $V_{CE(sat)}$ = 0.15V (typical). (I_C / I_B = 500mA / 50mA)
2) Complements the 2SB1132 / 2SB1237.

●Structure

Epitaxial planar type
NPN silicon transistor

●External dimensions (Units: mm)



* Denotes h_{FE}

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	40	V
Collector-emitter voltage		V_{CEO}	32	V
Emitter-base voltage		V_{EBO}	5	V
Collector current		I_C	1	A(DC)
			2	A(Pulse) *1
Collector power dissipation	2SD1664	P_C	0.5	
			2	W *2
	2SD1858		1	*3
Junction temperature		Tj	150	℃
Storage temperature		Tstg	−55~+150	℃

*1 Pw=20ms, duty=1 / 2
*2 When mounted on a 40 ×40×0.7 mm ceramic board.
*3 When it is mounted on the copper clad PCB (1.7mm thick) with land size for collector 1 square CM or larger.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	40	—	—	V	I_C=50 μA
Collector-emitter breakdown voltage	BV_{CEO}	32	—	—	V	I_C=1mA
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	I_E=50 μA
Collector cutoff current	I_{CBO}	—	—	0.5	μA	V_{CB}=20V
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	V_{EB}=4V
DC current transfer ratio	h_{FE}	82	—	390	—	V_{CE}=3V, I_C=100mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.15	0.4	V	I_C/I_B=500mA/50mA
Transition frequency	f_T	—	150	—	MHz	V_{CE}=5V, I_E=−50mA, f=100MHz
Output capacitance	Cob	—	15	—	pF	V_{CB}=10V, I_E=0A, f=1MHz

●Packaging specifications and h_{FE}

Type	h_{FE}	Package	Taping	
		Code	T100	TV2
		Basic ordering unit (pieces)	1000	2500
2SD1664	PQR		○	—
2SD1858	PQR		—	○

h_{FE} values are classified as follows :

Item	P	Q	R
h_{FE}	82～180	120～270	180～390

●Electrical characteristic curves

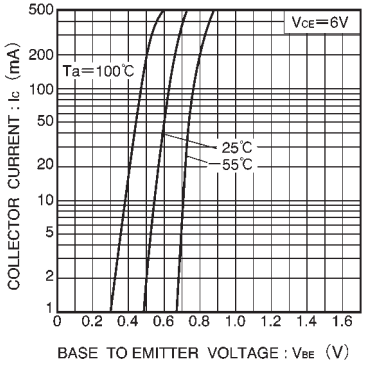


Fig.1 Grounded emitter propagation characteristics

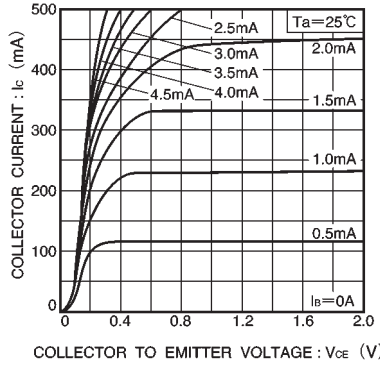


Fig.2 Grounded emitter output characteristics

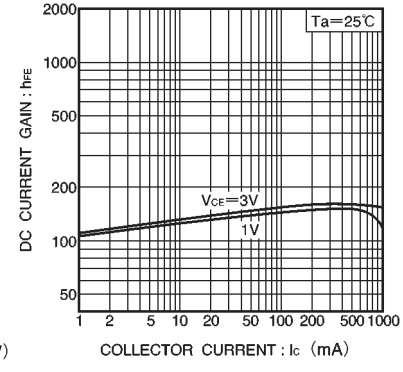


Fig.3 DC current gain vs. collector current (I)

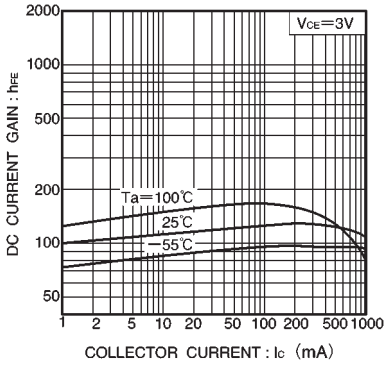


Fig.4 DC current gain vs. collector current (Ⅱ)

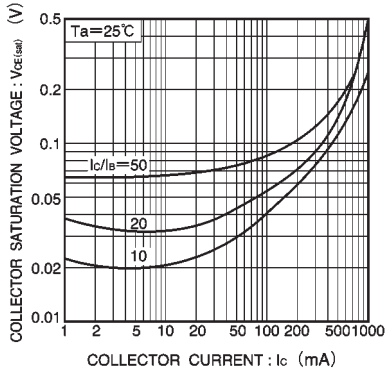


Fig.5 Collector-emitter saturation voltage vs. collector current (Ⅰ)

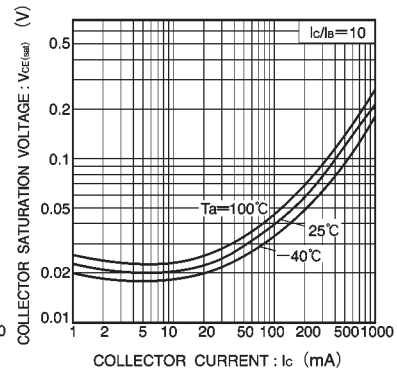


Fig.6 Collector-emitter saturation voltage vs. collector current (Ⅱ)

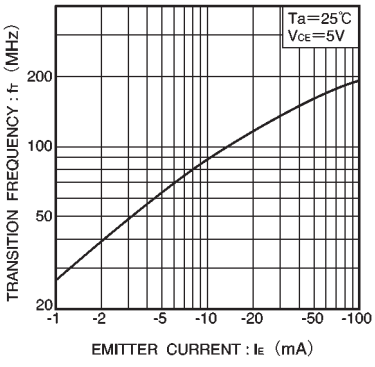


Fig.7 Gain bandwidth product vs. emitter current

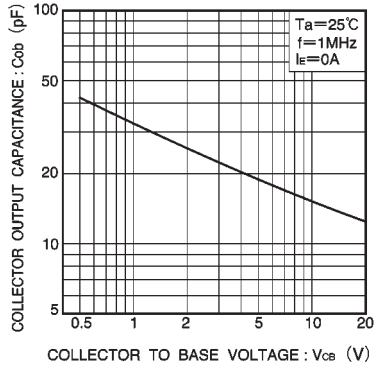


Fig.8 Collector output capacitance vs. collector-base voltage

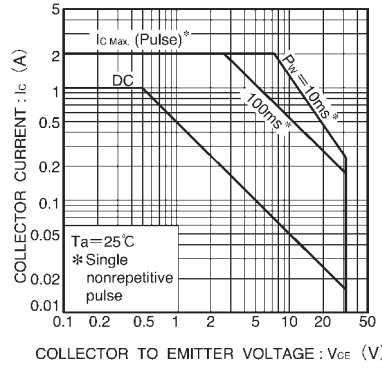


Fig.9 Safe operating area (2SD1664)

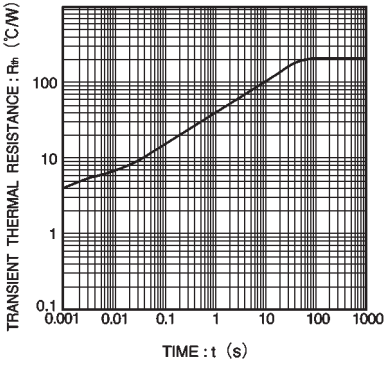


Fig.10 Transient thermal resistance (2SD1664)

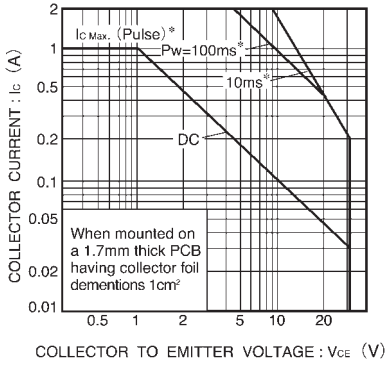


Fig.11 Safe operating area (2SD1858)

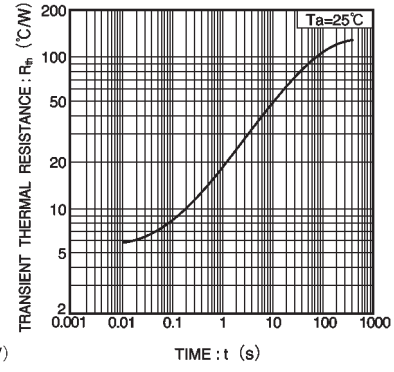


Fig.12 Transient thermal resistance (2SD1858)

Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the product described in this document are for reference only. Upon actual use, therefore, please request that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or otherwise dispose of the same, no express or implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document use silicon as a basic material.
  Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).
Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

About Export Control Order in Japan

Products described herein are the objects of controlled goods in Annex 1 (Item 16) of Export Trade Control Order in Japan.
In case of export from Japan, please confirm if it applies to "objective" criteria or an "informed" (by MITI clause) on the basis of "catch all controls for Non-Proliferation of Weapons of Mass Destruction.